

Mark: 2J

PNP Switching Transistor

This device is designed for very high speed saturated switching at collector currents to 100 mA. Sourced from Process 65. See PN4258 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--------------------------------------------------|-------------|-------|
| V _{CEO} | Collector-Emitter Voltage | 12 | V |
| V _{CBO} | Collector-Base Voltage | 12 | V |
| V _{EBO} | Emitter-Base Voltage | 4.0 | V |
| Ic | Collector Current - Continuous | 200 | mA |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

 1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations. 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol | Characteristic | Мах | | Units |
|-----------------|-----------------------------------------|--------|-----------|-------|
| | | PN3640 | *MMBT3640 | |
| P _D | Total Device Dissipation | 350 | 225 | mW |
| | Derate above 25°C | 2.8 | 1.8 | mW/∘C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 125 | | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 357 | 556 | °C/W |

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PN3640 / MMBT3640

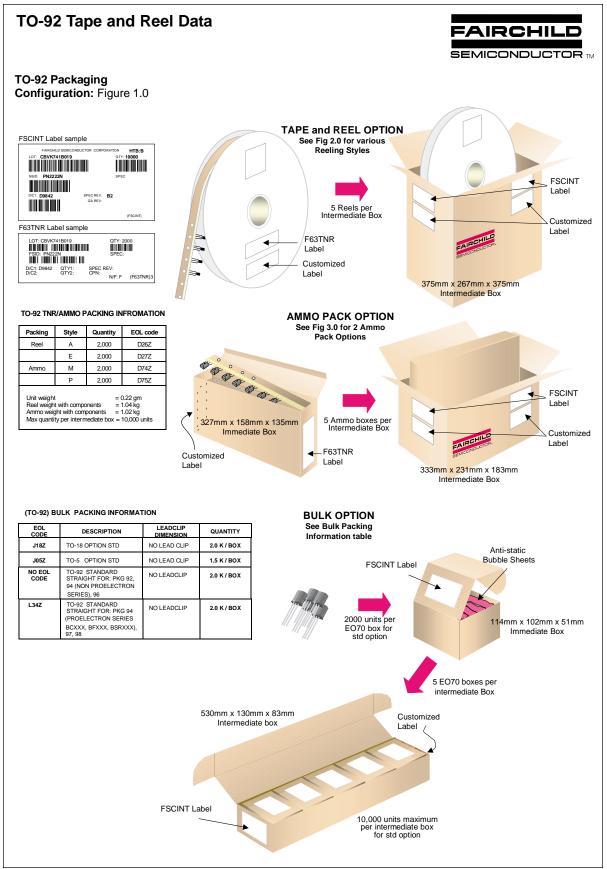
PNP Switching Transistor

| Symbol | Parameter | Test Conditions | Min | Max | Units |
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| | | | | | |
| | RACTERISTICS | | | | |
| / _{(BR)CEO} | Collector-Emitter Breakdown Voltage* | $I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$ | 12 | | V |
| / _{(BR)CES} | Collector-Emitter Breakdown Voltage | $I_{C} = 100 \ \mu A, \ V_{BE} = 0$ | 12 | | V |
| (BR)CBO | Collector-Base Breakdown Voltage | $I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$ | 12 | | V |
| / _{(BR)EBO} | Emitter-Base Breakdown Voltage | $I_{E} = 100 \ \mu A, I_{C} = 0$ | 4.0 | | V |
| CES | Collector Cutoff Current | $V_{CE} = 6.0 \text{ V}, V_{BE} = 0$ | | 0.01 1.0 | μΑ |
| В | Base Current | $V_{CE} = 6.0 \text{ V}, V_{BE} = 0, T_A = 65^{\circ}\text{C}$ $V_{CE} = 6.0 \text{ V}, V_{BE} = 0$ | | 1.0 | μA nA |
| , | | | | | |
|)N CHAR | RACTERISTICS* | | | | |
| | DC Current Gain | $I_{C} = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$ | 30 | 120 | |
| FE | | $I_{\rm C} = 50$ mA, $V_{\rm CE} = 0.0$ V | 20 | 120 | |
| / _{CE(sat)} | Collector-Emitter Saturation Voltage | $I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA | | 0.3 | V |
| | | $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ | | 0.2 0.6 | V V |
| | | $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}, T_{A} = 65^{\circ}\text{C}$ | | 0.25 | v |
| | | | | | |
| BE(sat) | Base-Emitter Saturation Voltage | $I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA | 0.75 | 0.95 | V |
| | Base-Emitter Saturation Voltage | $I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ | 0.75 0.8 | 0.95 1.0 1.5 | V V V |
| / _{BE(sat)} SMALL SI | | $I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ | | 1.0 | V |
| SMALL SI | GNAL CHARACTERISTICS Current Gain - Bandwidth Product | $I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ | 0.8 | 1.0 | V V |
| SMALL SI T Cobo | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance | $\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$ | 0.8 | 1.0 1.5 3.5 | MHz pF |
| SMALL SI | GNAL CHARACTERISTICS Current Gain - Bandwidth Product | $\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$ | 0.8 | 1.0 1.5 | V V MHz |
| SMALL SI T Cobo | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance | $\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$ | 0.8 | 1.0 1.5 3.5 | MHz pF |
| MALL SI | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS | $\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$ | 0.8 | 1.0 1.5 3.5 | MHz pF |
| MALL SI | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time | $\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$ | 0.8 | 1.0 1.5 3.5 | MHz pF |
| MALL SI Cobo Cibo | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time | $\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$ | 0.8 | 1.0 1.5 3.5 3.5 | MHz pF pF |
| SMALL SI Cobo Cibo SWITCHIN | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time | $\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$ | 0.8 | 1.0 1.5 3.5 3.5 10 | MHz pF pF |
| SMALL SI Pobo Dibo SWITCHIN | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time | $\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$ | 0.8 | 1.0 1.5 3.5 3.5 10 30 | MHz pF pF ns ns |
| SMALL SI r Pobo Pibo SWITCHIN d r s f | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time | $\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$ | 0.8 | 1.0 1.5 3.5 3.5 10 30 20 | MHz pF pF ns ns ns |
| SMALL SI Pobo Sibo SWITCHIN | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time | $\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \\ \end{split}$ | 0.8 | 1.0 1.5 3.5 3.5 10 30 20 12 | MHz pF pF ns ns ns ns |
| SMALL SI Pobo Sibo SWITCHIN | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time | $\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$ | 0.8 | 1.0 1.5 3.5 3.5 10 30 20 12 | MHz pF pF ns ns ns ns |
| SMALL SI Pobo Sibo SWITCHIN | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time Turn-On Time | $\begin{array}{c} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$ | 0.8 | 1.0 1.5 3.5 3.5 10 30 20 12 25 | MHz pF pF ns ns ns ns ns |
| SMALL SI Pobo Dibo Dibo SWITCHIN S S S S S S S S S S S S S S S S S S S | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time | $\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$ | 0.8 | 1.0 1.5 3.5 3.5 10 30 20 12 25 | MHz pF pF ns ns ns ns ns |
| SMALL SI r Cobo | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time Turn-On Time | $\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \\ \hline \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ V}, \\ f = 100 \text{ MHz} \\ \hline \\ V_{CB} = 5.0 \text{ V}, I_{E} = 0, \\ f = 1.0 \text{ MHz} \\ \hline \\ V_{BE} = 0.5 \text{ V}, I_{C} = 0, \\ f = 1.0 \text{ MHz} \\ \hline \\ V_{CC} = 6.0 \text{ V}, V_{BE(off)} = 1.9 \text{ V}, \\ I_{C} = 50 \text{ mA}, I_{B1} = 5.0 \text{ mA} \\ \hline \\ V_{CC} = 6.0 \text{ V}, I_{C} = 50 \text{ mA}, \\ I_{B1} = I_{B2} = 5.0 \text{ mA} \\ \hline \\ V_{CC} = 6.0 \text{ V}, V_{BE(off)} = 1.9 \text{ V}, \\ I_{C} = 50 \text{ mA}, I_{B1} = 5.0 \text{ mA} \\ \hline \\ V_{CC} = 1.5 \text{ V}, I_{C} = 10 \text{ mA}, \\ I_{B1} = I_{B2} = 0.5 \text{ mA} \\ \hline \\ V_{CC} = 6.0 \text{ V}, V_{BE(off)} = 1.9 \text{ V}, \\ I_{C} = 50 \text{ mA}, I_{B1} = 5.0 \text{ mA} \\ \hline \end{array}$ | 0.8 | 1.0 1.5 3.5 3.5 10 30 20 12 25 60 | MHz pF pF ns ns ns ns ns |
| SMALL SI T Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo Cobo | GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time Turn-On Time | $\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$ | 0.8 | 1.0 1.5 3.5 3.5 10 30 20 12 25 60 | MHz pF pF ns ns ns ns ns |

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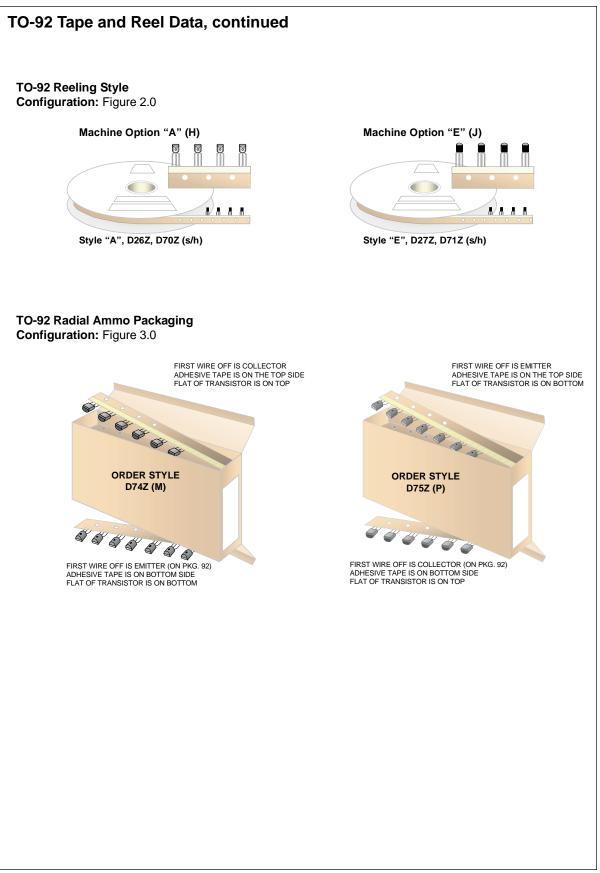
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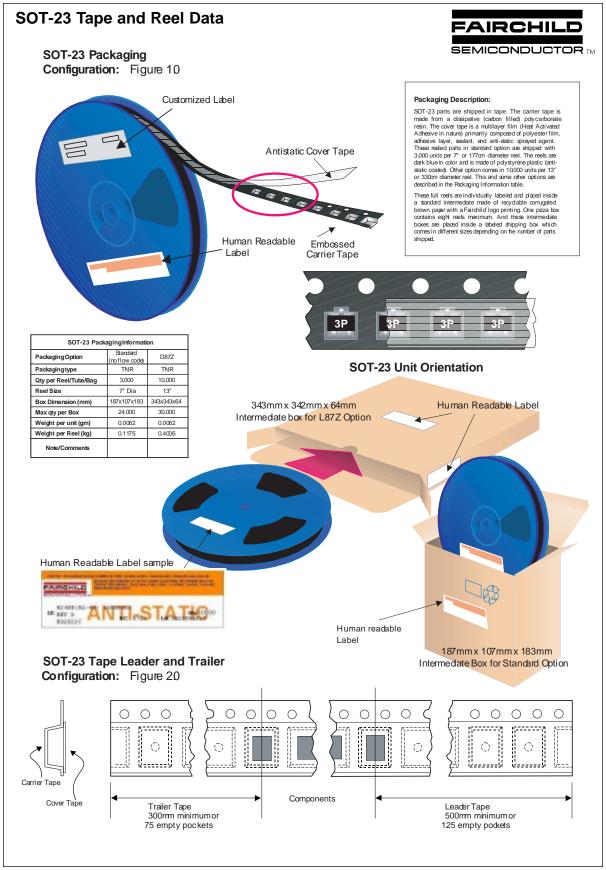
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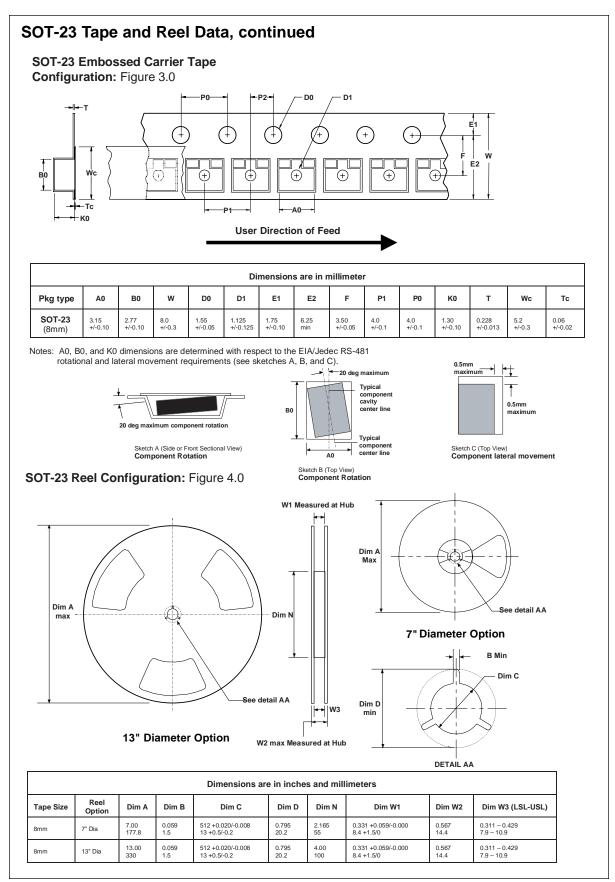
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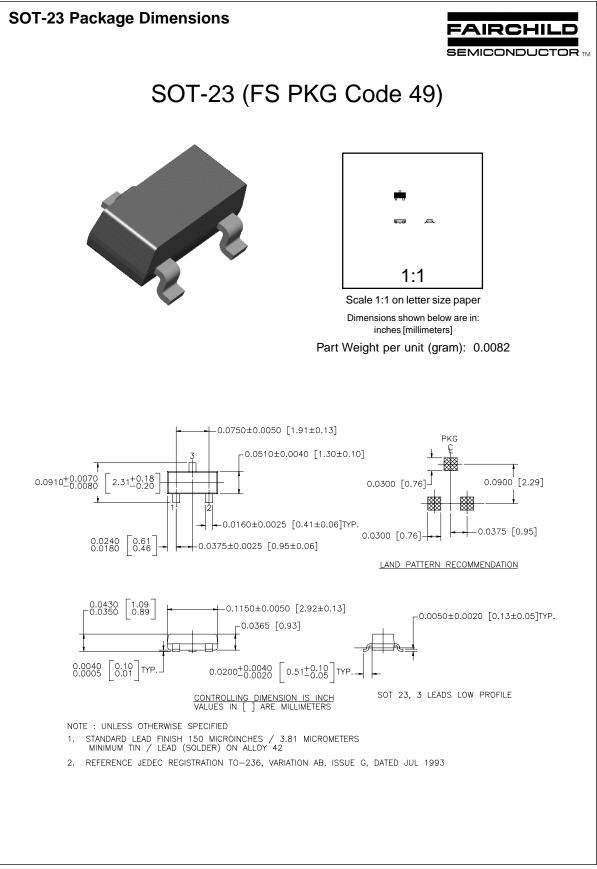


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| Datasheet Identification | Product Status | Definition |
|--------------------------|---------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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